RoHS

GREEN (5-2008)\*\*



## Vishay Semiconductors

## Silicon PIN Photodiode



#### **FEATURES**

Package type: leaded





• Radiant sensitive area (in mm<sup>2</sup>): 7.5

· High photo sensitivity

· High radiant sensitivity

· Suitable for visible and near infrared radiation

• Fast response times

• Angle of half sensitivity:  $\varphi = \pm 65^{\circ}$ 

 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



\*\* Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

#### **APPLICATIONS**

· High speed photo detector

## DESCRIPTION

BPW34 is a PIN photodiode with high speed and high radiant sensitivity in miniature, flat, top view, clear plastic package. It is sensitive to visible and near infrared radiation. BPW34S is packed in tubes, specifications like BPW34.

PRODUCT SUMMARY			
COMPONENT	I <sub>ra</sub> (μΑ)	φ (deg)	λ <sub>0.1</sub> (nm)
BPW34	50	± 65	430 to 1100
BPW34S	50	± 65	430 to 1100

#### Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	E PACKAGING REMARKS PACKAGE			
BPW34	Bulk	MOQ: 3000 pcs, 3000 pcs/bulk	Top view	
BPW34S	Tube	MOQ: 1800 pcs, 45 pcs/tube	Top view	

#### Note

• MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_{R}$	60	V
Power dissipation	T <sub>amb</sub> ≤ 25 °C	P <sub>V</sub>	215	mW
Junction temperature		Tj	100	°C
Operating temperature range		T <sub>amb</sub>	- 40 to + 100	°C
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C
Soldering temperature	t ≤ 3 s	T <sub>sd</sub>	260	°C
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm <sup>2</sup>	R <sub>thJA</sub>	350	K/W



# Vishay Semiconductors

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	I <sub>R</sub> = 100 μA, E = 0	V <sub>(BR)</sub>	60			V
Reverse dark current	V <sub>R</sub> = 10 V, E = 0	I <sub>ro</sub>		2	30	nA
Diode capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	C <sub>D</sub>		70		pF
	V <sub>R</sub> = 3 V, f = 1 MHz, E = 0	C <sub>D</sub>		25	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	TK <sub>Vo</sub>		- 2.6		mV/K
Chart aircuit aurrant	E <sub>A</sub> = 1 klx	l <sub>k</sub>		70		μA
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	l <sub>k</sub>		47		μA
Temperature coefficient of I <sub>k</sub>	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	TK <sub>lk</sub>		0.1		%/K
Reverse light current	E <sub>A</sub> = 1 klx, V <sub>R</sub> = 5 V	I <sub>ra</sub>		75		μA
	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_R = 5 \text{ V}$	I <sub>ra</sub>	40	50		μΑ
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		$\lambda_{p}$		900		nm
Range of spectral bandwidth		λ <sub>0.1</sub>		430 to 1100		nm
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4 x 10 <sup>-14</sup>		W/√Hz
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t <sub>r</sub>		100		ns
Fall time	$V_{R} = 10 \text{ V}, R_{L} = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t <sub>f</sub>		100		ns

## **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

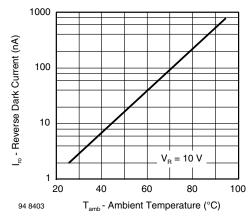


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

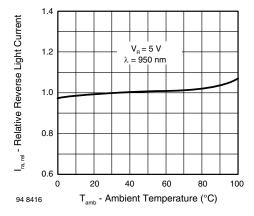
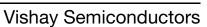


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature





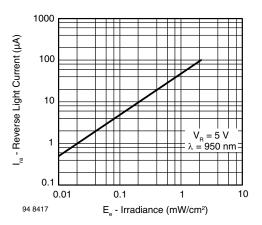


Fig. 3 - Reverse Light Current vs. Irradiance

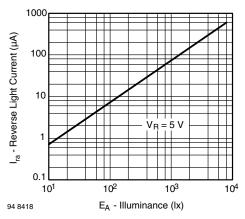


Fig. 4 - Reverse Light Current vs. Illuminance

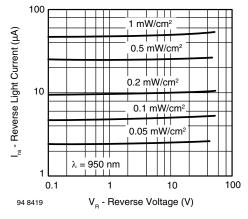


Fig. 5 - Reverse Light Current vs. Reverse Voltage

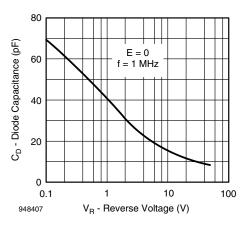


Fig. 6 - Diode Capacitance vs. Reverse Voltage

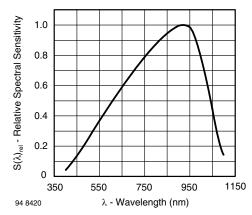


Fig. 7 - Relative Spectral Sensitivity vs. Wavelength

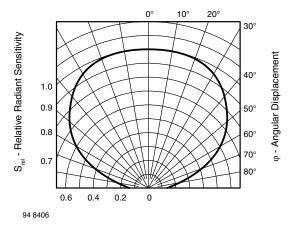
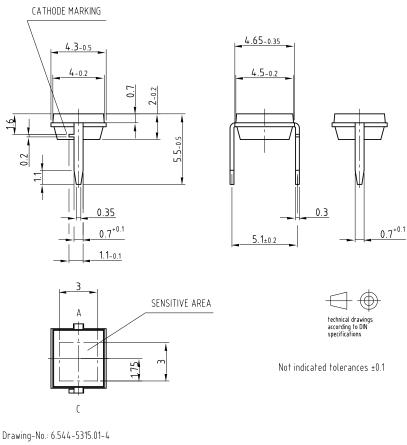


Fig. 8 - Relative Radiant Sensitivity vs. Angular Displacement

# Vishay Semiconductors

### **PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.544-5315.01-4 Issue: 1; 19.10.07 96 12186

### **TUBE PACKAGING DIMENSIONS** in millimeters

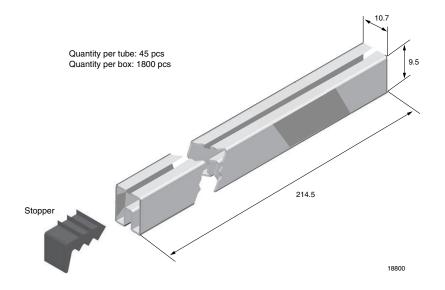


Fig. 9 - Drawing Proportions not scaled



## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.